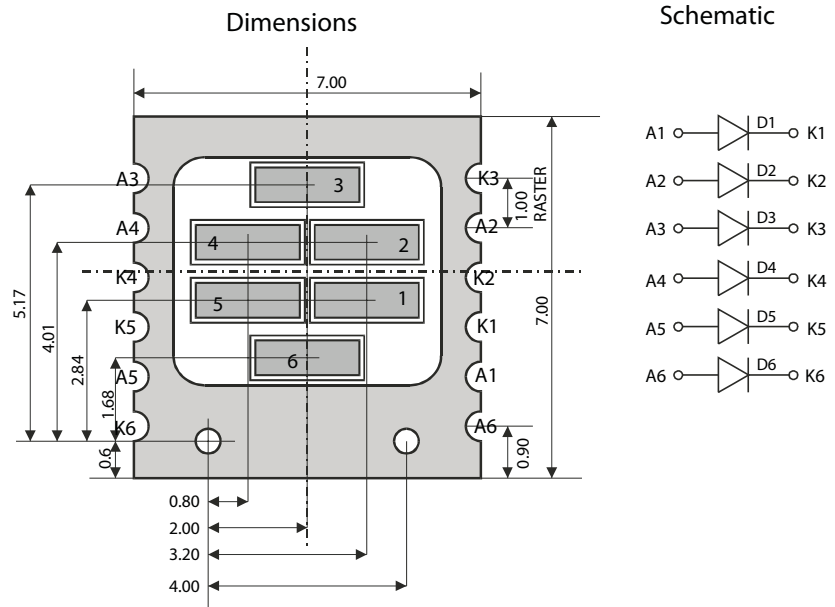


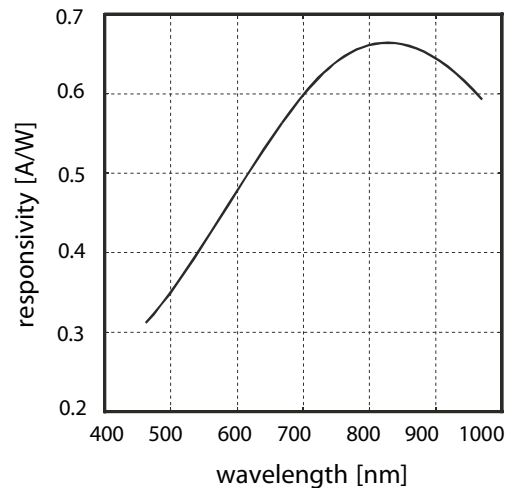
FEATURES

- High responsivity
- Low capacitance
- Suitable for SMT
- High reliability
- Peak wavelength at 830 nm



DESCRIPTION

The photosensor is made of 6-chip photodiode array. Photodiodes are produced in planar technology and passivated with silicon-nitride. Silicon-nitride is acting as antireflective layer. Photodiodes are bonded to the PCB and protected with transparent epoxy glue. The photodiode can work in photovoltaic or photoconductive mode.



TEMPERATURE CONDITIONS

Storage	-35 °C..+125 °C
Operating	-20 °C..+80 °C
Reflow soldering	220 °C, 60s

PHOTODIODE CHARACTERISTICS

DIODE	DIMENSIONS		ELECTRICAL PARAMETERS				OPTICAL PARAMETERS		
			DARK CURRENT	BV	CAPACITANCE		PEAK RESPONSE	CURRENT ¹	
TYPE	CHIP SIZE	ACTIVE AREA	$V_r = -5V$	$I_r > -50 \mu A$	$V_r = 0V$	$V_r = -5V$	I	CURRENT ¹	
			TYP	MIN	TYP	TYP	TYP		TYP
			(nA)	(V)	(pF)	(pF)	(nm)		(A/W)
FD 2309	2.3 x 0.9	1.46	<1	50	22	10	830	0.67	520

Note 1: CURRENT (I_{sc}) is measured under 100 mW/cm² AM spectrum.